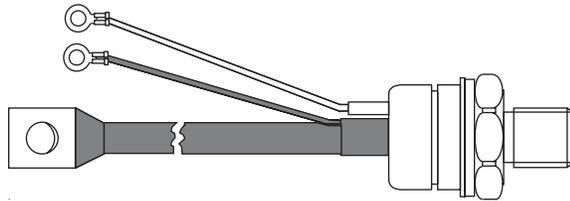


## Inverter Grade Thyristors (Stud Version), 175 A



TO-209AB (TO-93)

**FEATURES**

- All diffused design
- Center amplifying gate
- Guaranteed high dV/dt
- Guaranteed high dI/dt
- High surge current capability
- Low thermal impedance
- High speed performance
- Compression bonding
- Lead (Pb)-free
- Designed and qualified for industrial level


**RoHS  
COMPLIANT**
**PRODUCT SUMMARY**

$I_{T(AV)}$	175 A
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**TYPICAL APPLICATIONS**

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

**MAJOR RATINGS AND CHARACTERISTICS**

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		175	A
	$T_C$	85	°C
$I_{T(RMS)}$		275	A
$I_{TSM}$	50 Hz	4680	
	60 Hz	4900	
$I^2t$	50 Hz	110	kA <sup>2</sup> s
	60 Hz	100	
$V_{DRM}/V_{RRM}$		1000 to 1200	V
$t_q$	Range	15 to 25	µs
$T_J$		- 40 to 125	°C

**ELECTRICAL SPECIFICATIONS**
**VOLTAGE RATINGS**

TYPE NUMBER	VOLTAGE CODE	$V_{DRM}/V_{RRM}$ , MAXIMUM REPETITIVE PEAK VOLTAGE V	$V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA
ST173S	10	1000	1100	40
	12	1200	1300	

# ST173SPbF Series



Vishay High Power Products Inverter Grade Thyristors  
(Stud Version), 175 A

CURRENT CARRYING CAPABILITY							
FREQUENCY							UNITS
50 Hz	500	320	790	550	4510	3310	A
400 Hz	450	290	810	540	1970	1350	
1000 Hz	330	190	760	490	1050	680	
2500 Hz	170	80	510	300	480	280	
Recovery voltage $V_r$	50		50		50		V
Voltage before turn-on $V_d$	$V_{DRM}$		$V_{DRM}$		$V_{DRM}$		
Rise of on-state current $di/dt$	50		-		-		A/ $\mu$ s
Case temperature	60	85	60	85	60	85	$^{\circ}$ C
Equivalent values for RC circuit	47/0.22		47/0.22		47/0.22		$\Omega/\mu$ F

ON-STATE CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current at case temperature	$I_{T(AV)}$	180 $^{\circ}$ conduction, half sine wave		175	A	
				85	$^{\circ}$ C	
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 75 $^{\circ}$ C case temperature		275		
Maximum peak, one half cycle, non-repetitive surge current	$I_{TSM}$	t = 10 ms	No voltage reappplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	4680	A
		t = 8.3 ms			4900	
		t = 10 ms	100 % $V_{RRM}$ reappplied		3940	
		t = 8.3 ms			4120	
Maximum $I^2t$ for fusing	$I^2t$	t = 10 ms	No voltage reappplied		110	kA $^2$ s
		t = 8.3 ms			100	
		t = 10 ms	100 % $V_{RRM}$ reappplied		77	
		t = 8.3 ms			71	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reappplied		1100	kA $^2\sqrt{s}$	
Maximum peak on-state voltage	$V_{TM}$	$I_{TM} = 600$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine wave pulse		2.07	V	
Low level value of threshold voltage	$V_{T(TO)1}$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		1.55		
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		1.58		
Low level value of forward slope resistance	$r_{t1}$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		0.87	m $\Omega$	
High level value of forward slope resistance	$r_{t2}$	$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		0.82		
Maximum holding current	$I_H$	$T_J = 25$ $^{\circ}$ C, $I_T > 30$ A		600	mA	
Typical latching current	$I_L$	$T_J = 25$ $^{\circ}$ C, $V_A = 12$ V, $R_a = 6$ $\Omega$ , $I_G = 1$ A		1000		

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum non-repetitive rate of rise of turned on current	$di/dt$	$T_J = T_J$ maximum, $V_{DRM} = \text{Rated } V_{DRM}$ $I_{TM} = 2 \times di/dt$		1000	A/ $\mu$ s
Typical delay time	$t_d$	$T_J = 25$ $^{\circ}$ C, $V_{DM} = \text{Rated } V_{DRM}$ , $I_{TM} = 50$ A DC, $t_p = 1$ $\mu$ s Resistive load, gate pulse: 10 V, 5 $\Omega$ source		1.1	$\mu$ s
Maximum turn-off time	minimum	$T_J = T_J$ maximum, $I_{TM} = 300$ A, commutating $di/dt = 20$ A/ $\mu$ s $V_R = 50$ V, $t_p = 500$ $\mu$ s, $dV/dt$ : See table in device code		15	
	maximum			25	



<b>BLOCKING</b>				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum, linear to 80 % V <sub>DRM</sub> , higher value available on request	500	V/μs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, rated V <sub>DRM</sub> /V <sub>RRM</sub> applied	40	mA

<b>TRIGGERING</b>				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, f = 50 Hz, d% = 50	60	W
Maximum average gate power	P <sub>G(AV)</sub>		10	
Maximum peak positive gate current	I <sub>GM</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, t <sub>p</sub> ≤ 5 ms	10	A
Maximum peak positive gate voltage	+ V <sub>GM</sub>		20	V
Maximum peak negative gate voltage	- V <sub>GM</sub>		5	
Maximum DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C, V <sub>A</sub> = 12 V, R <sub>a</sub> = 6 Ω	200	mA
Maximum DC gate voltage required to trigger	V <sub>GT</sub>		3	V
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = T <sub>J</sub> maximum, rated V <sub>DRM</sub> applied	20	mA
Maximum DC gate voltage not to trigger	V <sub>GD</sub>		0.25	V

<b>THERMAL AND MECHANICAL SPECIFICATIONS</b>				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	T <sub>J</sub>		- 40 to 125	°C
Maximum storage temperature range	T <sub>Stg</sub>		- 40 to 150	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	0.105	K/W
Maximum thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.04	
Mounting torque, ± 10 %		Non-lubricated threads	31 (275)	N · m (lbf · in)
		Lubricated threads	24.5 (210)	
Approximate weight			280	g
Case style		See dimensions - link at the end of datasheet	TO-209AB (TO-93)	

<b>ΔR<sub>thJC</sub> CONDUCTION</b>				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.016	0.012	T <sub>J</sub> = T <sub>J</sub> maximum	K/W
120°	0.019	0.020		
90°	0.025	0.027		
60°	0.036	0.037		
30°	0.060	0.060		

**Note**

- The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

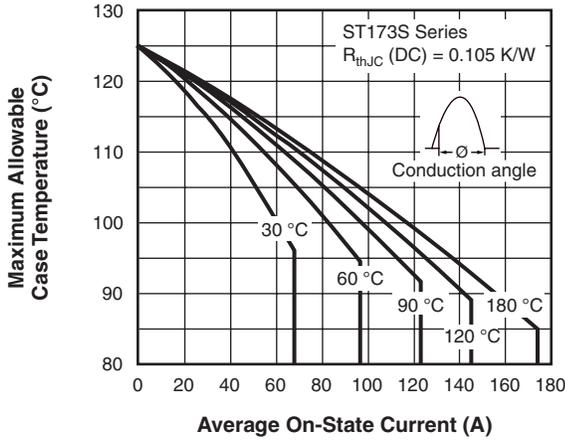


Fig. 1 - Current Ratings Characteristics

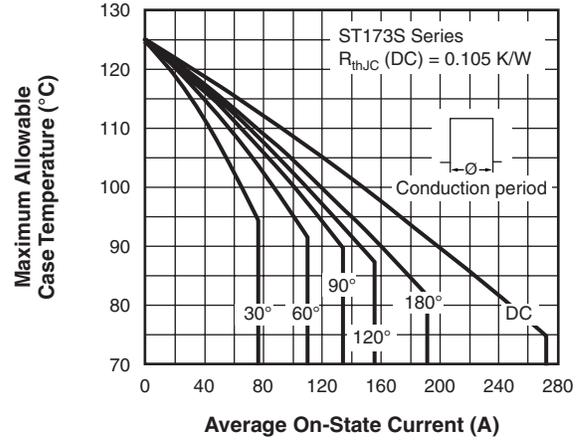


Fig. 2 - Current Ratings Characteristics

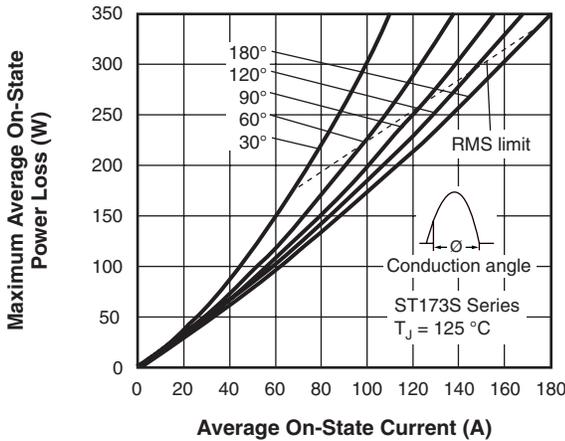


Fig. 3 - On-State Power Loss Characteristics

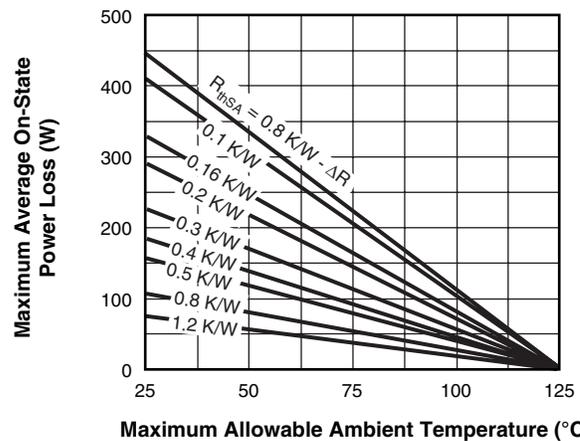
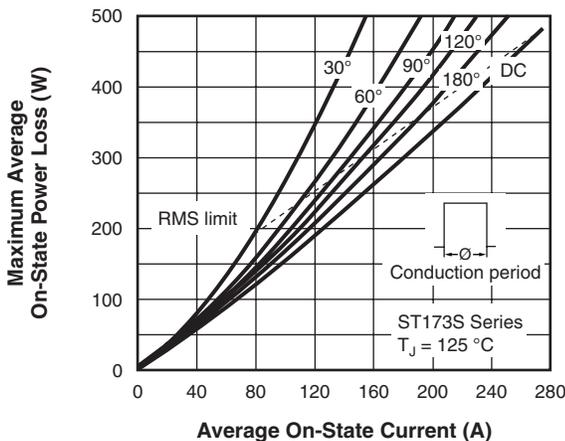
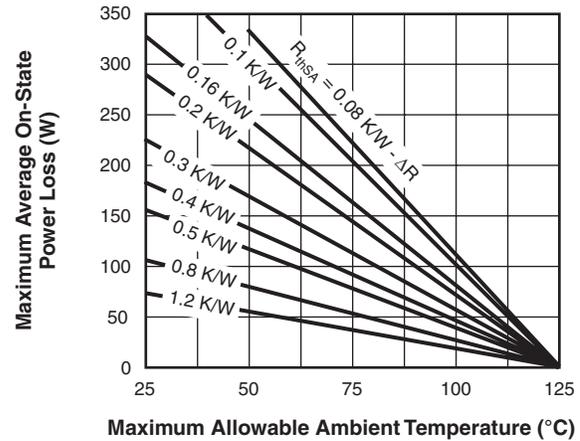


Fig. 4 - On-State Power Loss Characteristics

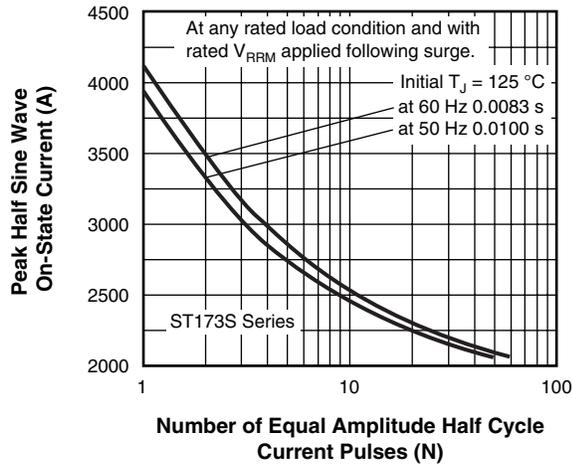


Fig. 5 - Maximum Non-Repetitive Surge Current

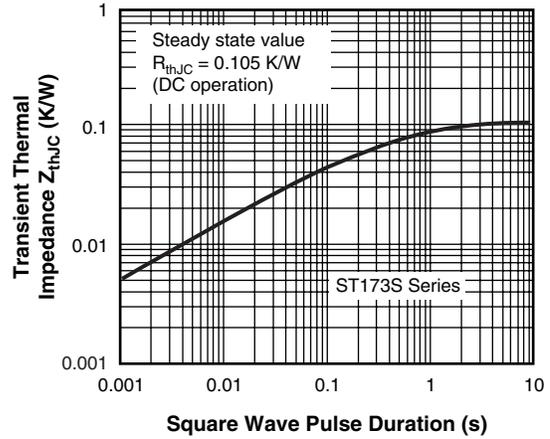


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

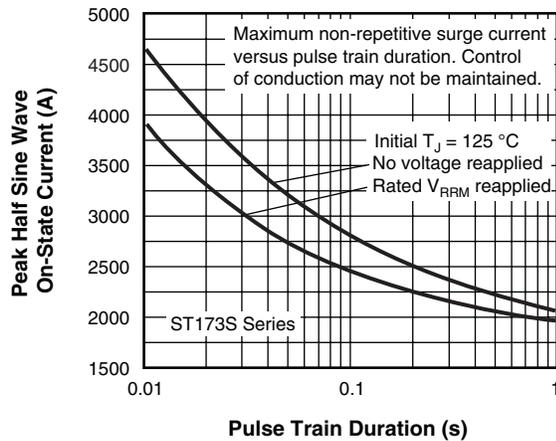


Fig. 6 - Maximum Non-Repetitive Surge Current

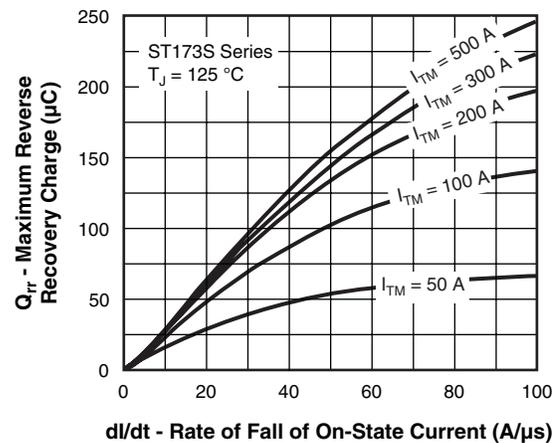


Fig. 9 - Reverse Recovered Current Characteristics

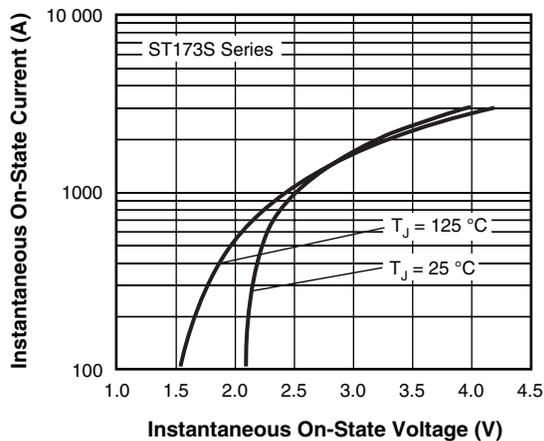


Fig. 7 - On-State Voltage Drop Characteristics

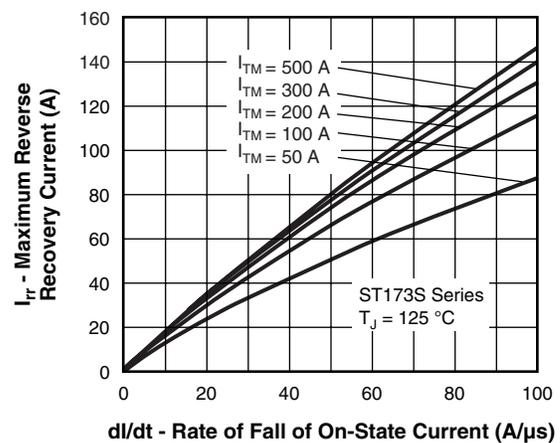


Fig. 10 - Reverse Recovery Current Characteristics

# ST173SPbF Series

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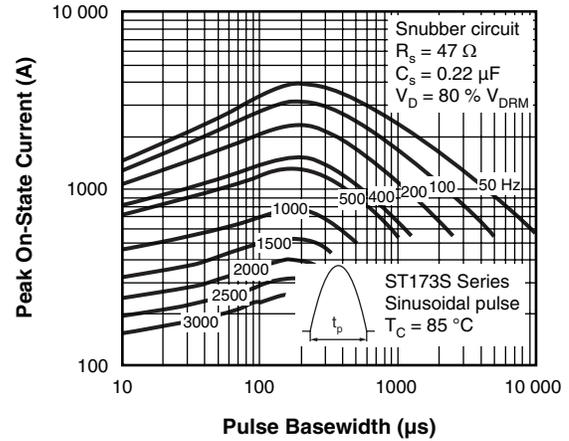
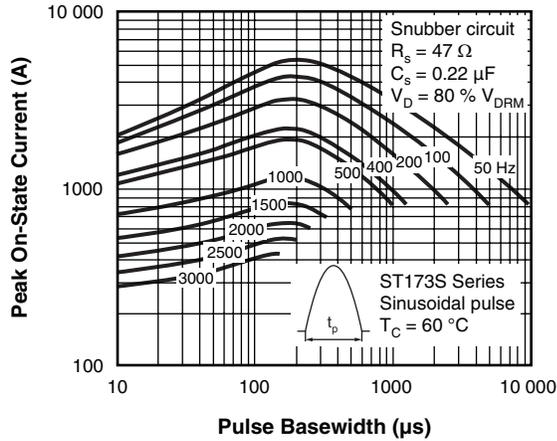


Fig. 11 - Frequency Characteristics

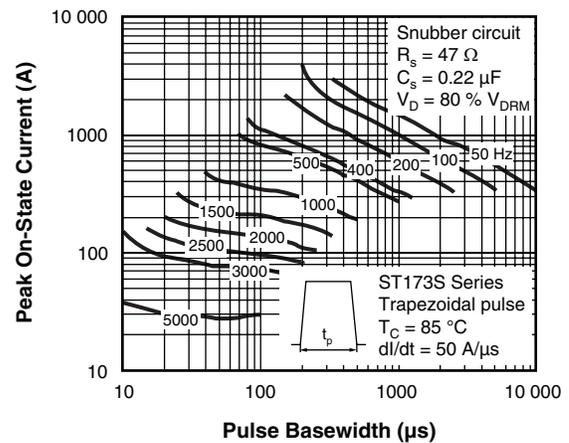
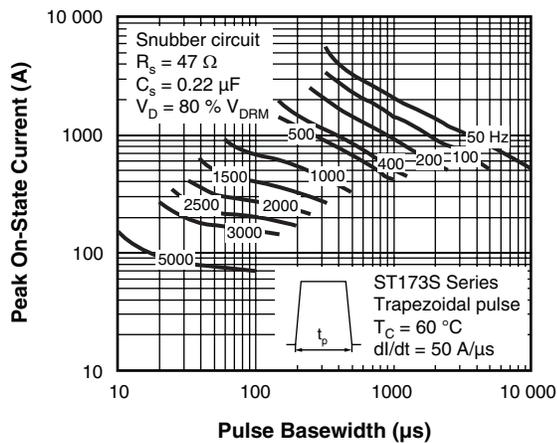


Fig. 12 - Frequency Characteristics

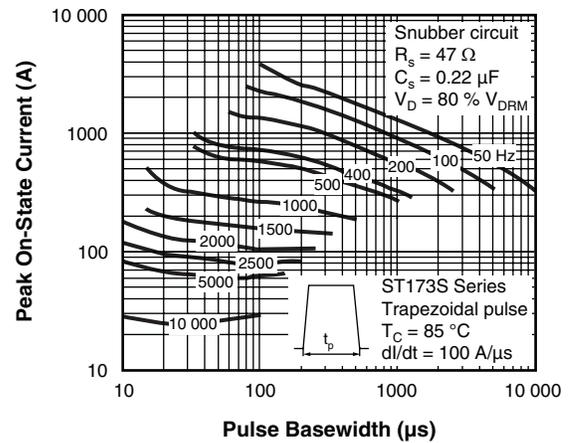
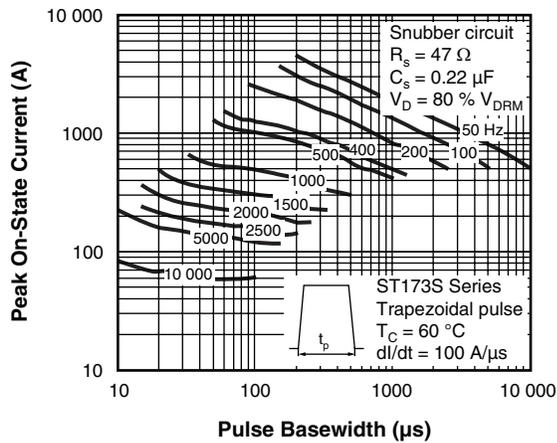


Fig. 13 - Frequency Characteristics

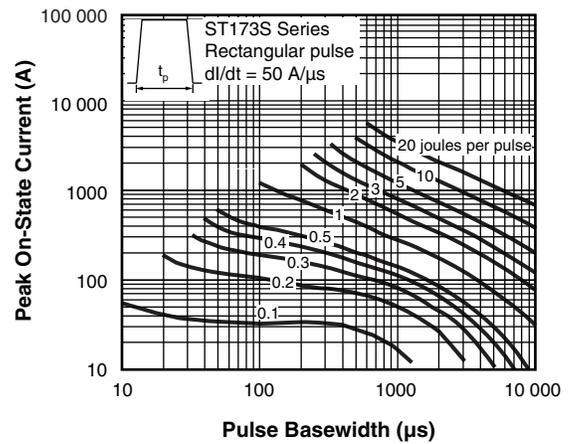
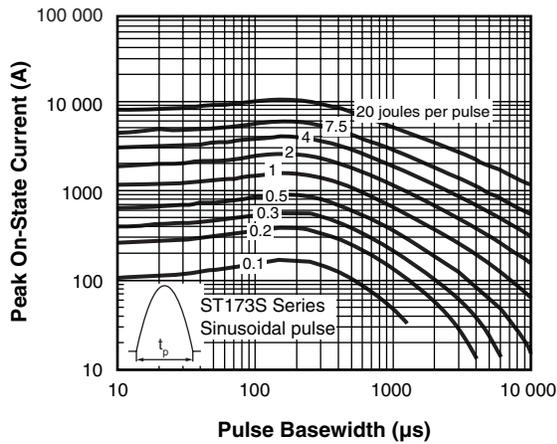


Fig. 14 - Maximum On-State Energy Power Loss Characteristics

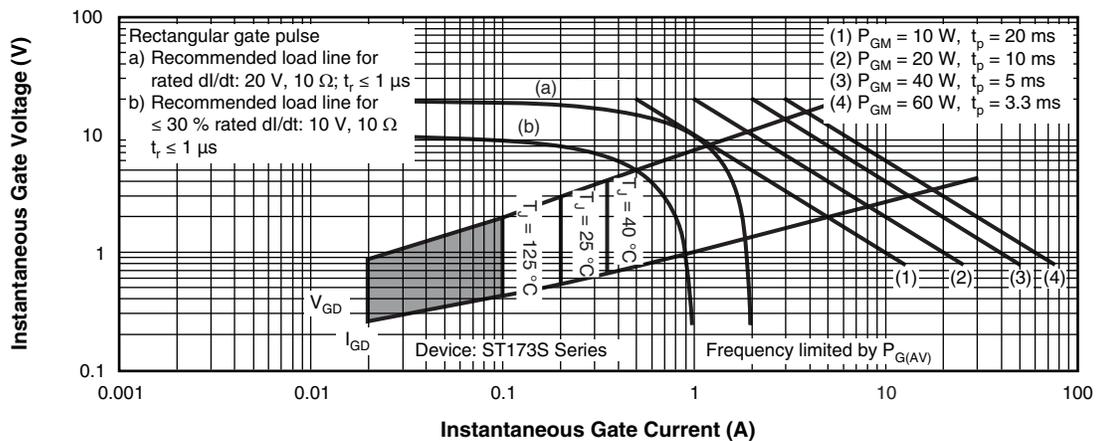


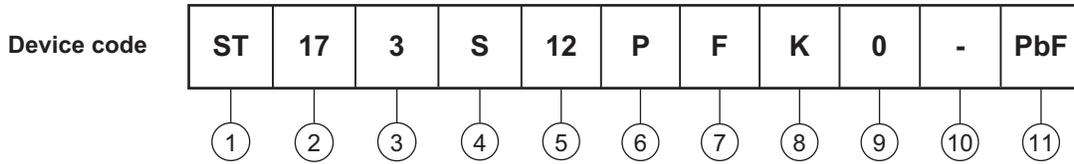
Fig. 15 - Gate Characteristics

# ST173SPbF Series



Vishay High Power Products Inverter Grade Thyristors  
(Stud Version), 175 A

## ORDERING INFORMATION TABLE



- 1** - Thyristor
- 2** - Essential part number
- 3** - 3 = Fast turn-off
- 4** - S = Compression bonding stud
- 5** - Voltage code x 100 =  $V_{RRM}$  (see Voltage Ratings table)
- 6** - P = Stud base 3/4" 16UNF-2A  
M = Stud base metric threads M16 x 1.5
- 7** - Reapplied dV/dt code (for  $t_q$  test condition)
- 8** -  $t_q$  code
- 9** - 0 = Eyelet terminals  
(gate and aux. cathode leads)  
1 = Fast-on terminals  
(gate and aux. cathode leads)  
2 = Flag terminals (for cathode and gate terminals)
- 10** - Critical dV/dt:
  - None = 500 V/ $\mu$ s (standard value)
  - L = 1000 V/ $\mu$ s (special selection)
- 11** - Lead (Pb)-free

dV/dt - $t_q$ combinations available						
	dV/dt (V/ $\mu$ s)	20	50	100	200	400
$t_q$ ( $\mu$ s)	15	CL	-	-	-	-
	18	CP	DP	EP	<b>FP*</b>	-
	20	CK	DK	EK	<b>FK*</b>	HK
	25	CJ	DJ	EJ	FJ	HJ
	30	-	DH	EH	FH	HH

\* Standard part number.  
All other types available only on request.

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95079">http://www.vishay.com/doc?95079</a>



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